



Transport in epitaxial graphene on the nanoscale

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Time: 4:00pm, Jan. 18, 2019 (Friday)

时间: 2019年1月18日 (周五) 下午4:00

Venue: Room W663, Physics building, Peking University

地点: 北京大学物理楼, 西663会议室

Abstract

The transport properties of epitaxial graphene have been subject of intense theoretical and experimental investigations since its invention. Besides electron-electron and electron-phonon scattering, the charge transport is determined by structural defects such as impurities, substrate steps or monolayer/bilayer junctions. The latter are leading to a spatially varying potential landscape as well as a T_{fi} 0 0 1 442.3 82.27 TmC

About the speaker

Education:

1982 - 1988 Study of Physics at the University of Dortmund

1988 Diploma in Physics

1988 - 1992 Ph.D. in Physics, Georg - August - University of Göttingen

2017 Habilitation in Physics, Georg - August - University of Göttingen

Employment:

1992 - today Akademischer Rat, Georg - August - University of Göttingen

Areas of Research:

Correlation effects in electronic and magnetic systems

Transport in ultra - thin films

Single impurities in semiconductors and in metals

Semiconductor heterostructures

Compound systems of magnetic metals on semiconductors

Nano scale characterization based on scanning probe techniques (e.g. crosssectional STM/STS/STP at low temperature)